The New Generation Laser Dicing Tehcnology for Ultra Thin Si wafer

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New Generation Laser Dicing Technology for Ultra Thin Si Wafer

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1

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Background

- **♦INHERENT PROBLEM of BLADE DICING**
 - ■undesirable mechanical stress

>It is difficult that dicing processing speed become higher or wafer thickness become thinner.

But, Wafer will be thinner

100 μm \Rightarrow 50 μm \Rightarrow 30 μm

>>> LASER DICING!!



2

ISMP2006 **Laser Dicing Stealth Dicing (SD) Ablation method Processing** Processing on the surface in the inside **Debris** ())))))), Wafer ■Debris contamination ■No debris contamination Cleaning process ■No cleaning process ■Cut loss ■Less cut loss

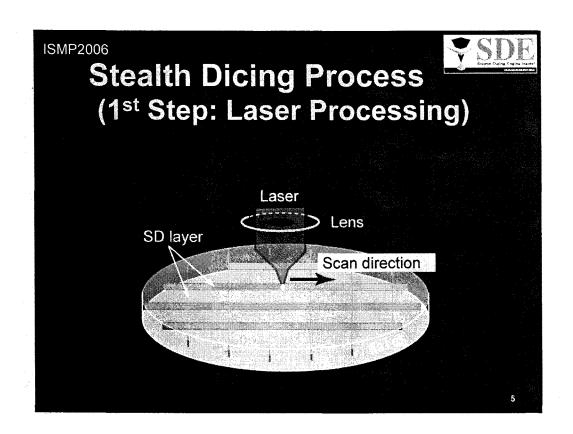
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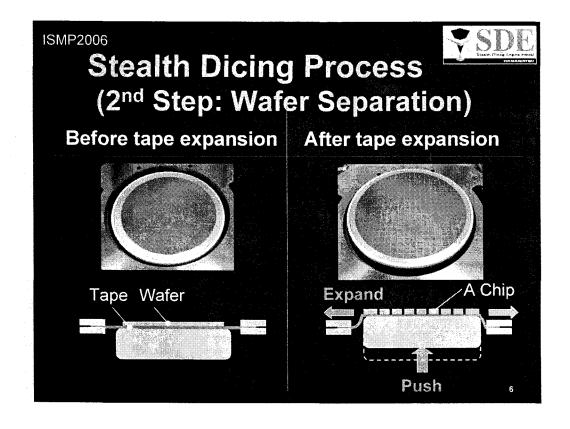


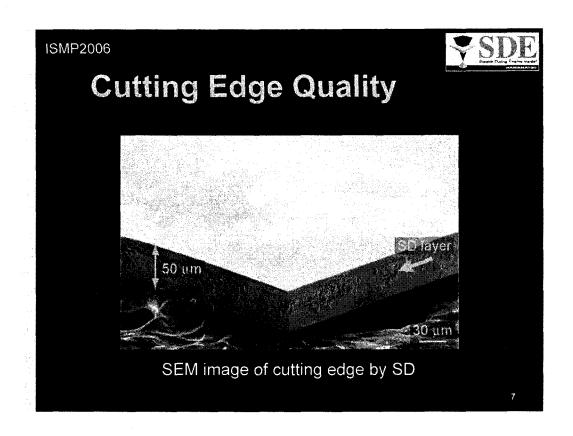
Advantages of SD

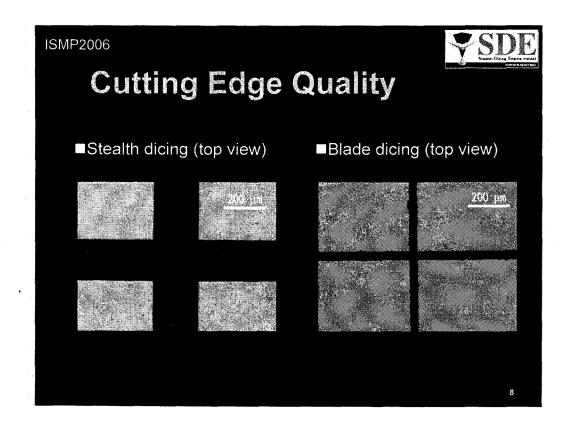
- 1. High Speed dicing for thinner wafers without chipping.
- No debris contaminants and no creating damages on the surface.
- 3. Completely dry process.

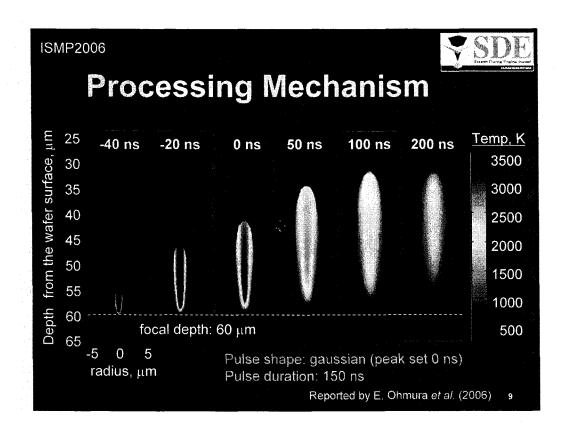
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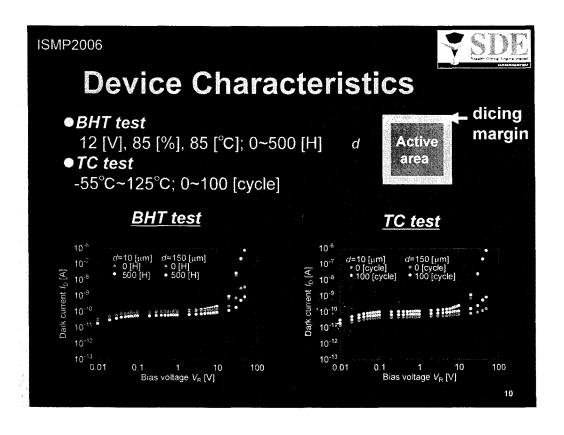


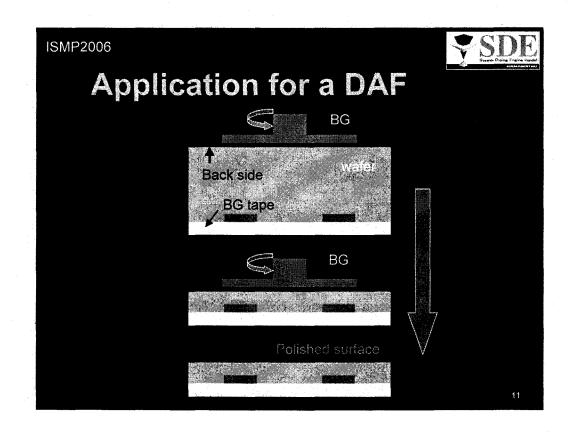


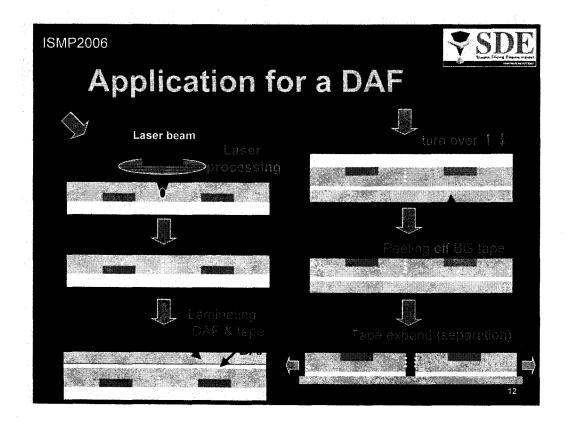


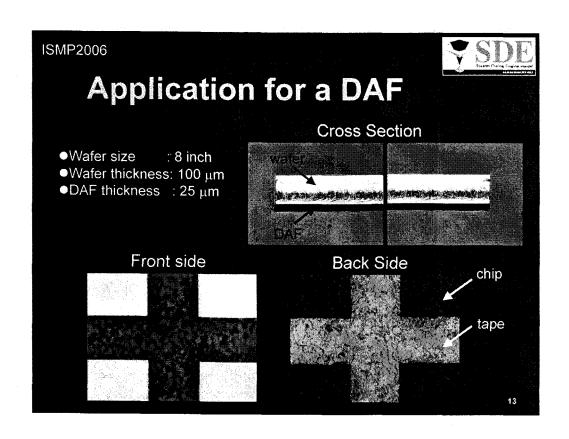


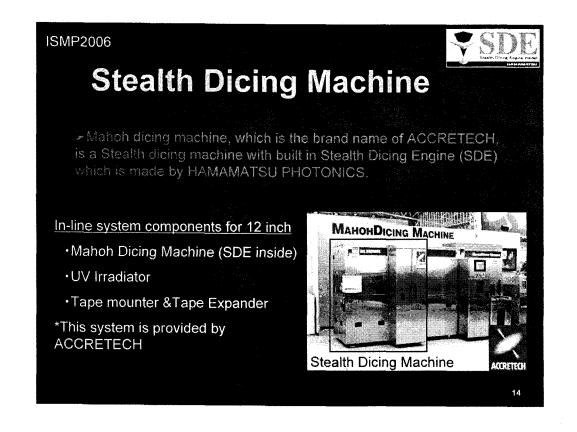












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Summary

Process & mechanism

- ◆The process consists from two steps which are laser processing step and separation step.
- ◆The wavelength of laser beam is transmissible wavelength for the wafer. However, inside of Si wafer is processed due to temperature dependence of optical absorption coefficient

15

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Summary



Advantage & Application

- ◆Advantages are high speed dicing, no debris contaminants, completely dry process, etc.
- ◆The cutting edges were fine. The lifetime and endurances did not degrade the device characteristics
- ◆A separation of a wafer with DAF was introduced as an application for SiP

16